

IGBT XPT Module

H Bridge

$$V_{CES} = 1200 \text{ V}$$

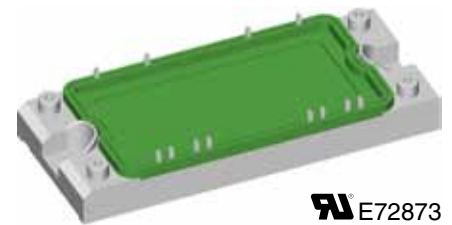
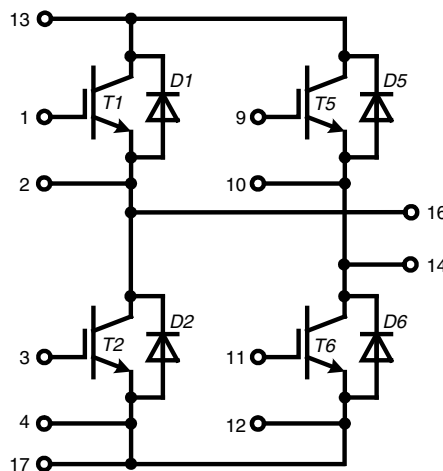
$$I_{C25} = 85 \text{ A}$$

$$V_{CE(sat)} = 1.8 \text{ V}$$

Preliminary data

Part name (Marking on product)

MIXA 61H1200ED



Features:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
 - short circuit rated for 10 μsec .
 - very low gate charge
 - square RBSOA @ $3 \times I_C$
 - low EMI
- Thin wafer technology combined with the XPT design results in a competitive low $V_{CE(sat)}$
- SONIC™ diode
 - fast and soft reverse recovery
 - low operating forward voltage

Application:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies

Package:

- "E2-Pack" standard outline
- Insulated copper base plate
- Soldering pins for PCB mounting

Output Inverter T1 - T6

| Symbol | Definitions | Conditions | Ratings | | | Unit | |
|---------------|---------------------------------------|--|---|------------|----------|---------------|----------|
| | | | min. | typ. | max. | | |
| V_{CES} | collector emitter voltage | | $T_{VJ} = 25^{\circ}\text{C}$ | | 1200 | V | |
| V_{GES} | max. DC gate voltage | continuous | | | ± 20 | V | |
| V_{GEM} | max. transient collector gate voltage | transient | | | ± 30 | V | |
| I_{C25} | collector current | | $T_C = 25^{\circ}\text{C}$ | | 85 | A | |
| I_{C80} | | | $T_C = 80^{\circ}\text{C}$ | | 60 | A | |
| P_{tot} | total power dissipation | | $T_C = 25^{\circ}\text{C}$ | | 290 | W | |
| $V_{CE(sat)}$ | collector emitter saturation voltage | $I_C = 55\text{ A}; V_{GE} = 15\text{ V}$ | $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$ | 1.8 2.1 | 2.1 | V V | |
| $V_{GE(th)}$ | gate emitter threshold voltage | $I_C = 2\text{ mA}; V_{GE} = V_{CE}$ | $T_{VJ} = 25^{\circ}\text{C}$ | 5.4 | 6.0 | 6.5 | V |
| I_{CES} | collector emitter leakage current | $V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$ | $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$ | | 0.5 | 0.2 | mA mA |
| I_{GES} | gate emitter leakage current | $V_{GE} = \pm 20\text{ V}$ | | | 500 | nA | |
| $Q_{G(on)}$ | total gate charge | $V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 50\text{ A}$ | | | 165 | nC | |
| $t_{d(on)}$ | turn-on delay time | inductive load $V_{CE} = 600\text{ V}; I_C = 50\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 15\ \Omega$ | $T_{VJ} = 125^{\circ}\text{C}$ | | 70 | ns | |
| t_r | current rise time | | | | 40 | ns | |
| $t_{d(off)}$ | turn-off delay time | | | | 250 | ns | |
| t_f | current fall time | | | | 100 | ns | |
| E_{on} | turn-on energy per pulse | | | | 4.5 | mJ | |
| E_{off} | turn-off energy per pulse | | | | 5.5 | mJ | |
| RBSOA | reverse bias safe operating area | $V_{GE} = \pm 15\text{ V}; R_G = 15\ \Omega;$ | $T_{VJ} = 125^{\circ}\text{C}$ $V_{CEK} = 1200\text{ V}$ | | 150 | A | |
| SCSOA | short circuit safe operating area | | $T_{VJ} = 125^{\circ}\text{C}$ | | 10 | μs | |
| t_{SC} | short circuit duration | $V_{CE} = 900\text{ V}; V_{GE} = \pm 15\text{ V};$ $R_G = 15\ \Omega;$ non-repetitive | | | 200 | A | |
| I_{SC} | short circuit current | | | | | | |
| R_{thJC} | thermal resistance junction to case | (per IGBT) | | | 0.43 | K/W | |

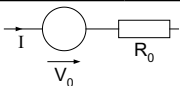
Output Inverter D1 - D6

| Symbol | Definitions | Conditions | Ratings | | | Unit |
|------------|-------------------------------------|--|---|--------------|------|---------------|
| | | | min. | typ. | max. | |
| V_{RRM} | max. repetitive reverse voltage | | $T_{VJ} = 25^{\circ}\text{C}$ | | 1200 | V |
| I_{F25} | forward current | | $T_C = 25^{\circ}\text{C}$ | | 85 | A |
| I_{F80} | | | $T_C = 80^{\circ}\text{C}$ | | 57 | A |
| V_F | forward voltage | $I_F = 60\text{ A}; V_{GE} = 0\text{ V}$ | $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$ | 1.95 1.95 | 2.2 | V V |
| Q_{rr} | reverse recovery charge | $V_R = 600\text{ V}$ $di_f/dt = -1200\text{ A}/\mu\text{s}$ $I_F = 60\text{ A}; V_{GE} = 0\text{ V}$ | $T_{VJ} = 125^{\circ}\text{C}$ | | 8 | μC |
| I_{RM} | max. reverse recovery current | | | | 60 | A |
| t_{rr} | reverse recovery time | | | | 350 | ns |
| E_{rec} | reverse recovery energy | | | | 2.5 | mJ |
| R_{thJC} | thermal resistance junction to case | (per diode) | | | 0.6 | K/W |

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Module

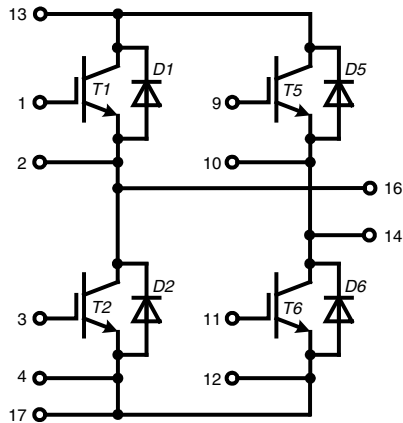
| Symbol | Definitions | Conditions | Ratings | | | Unit |
|----------------|-------------------------------------|--|---------|------|------|------|
| | | | min. | typ. | max. | |
| T_{VJ} | operating temperature | | -40 | | 125 | °C |
| T_{VJM} | max. virtual junction temperature | | | | 150 | °C |
| T_{stg} | storage temperature | | -40 | | 125 | °C |
| V_{ISOL} | isolation voltage | $I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$ | | | 3000 | V~ |
| CTI | comparative tracking index | | | | - | |
| M_d | mounting torque (M5) | | 3 | | 6 | Nm |
| d_s | creep distance on surface | | 6 | | | mm |
| d_A | strike distance through air | | 6 | | | mm |
| $R_{pin-chip}$ | resistance pin to chip | | | 5 | | mΩ |
| R_{thCH} | thermal resistance case to heatsink | with heatsink compound | | 0.02 | | K/W |
| Weight | | | | 180 | | g |

Equivalent Circuits for Simulation


| Symbol | Definitions | Conditions | min. | Ratings | | Unit |
|----------------|---------------------|------------|------------------------------|---------------|------|---------|
| | | | | typ. | max. | |
| V_0 R_0 | IGBT | T1 - T6 | $T_{VJ} = 150^\circ\text{C}$ | 1.1 | | V mΩ |
| V_0 R_0 | free wheeling diode | D1 - D6 | $T_{VJ} = 150^\circ\text{C}$ | 1.22 12.99 | | V mΩ |

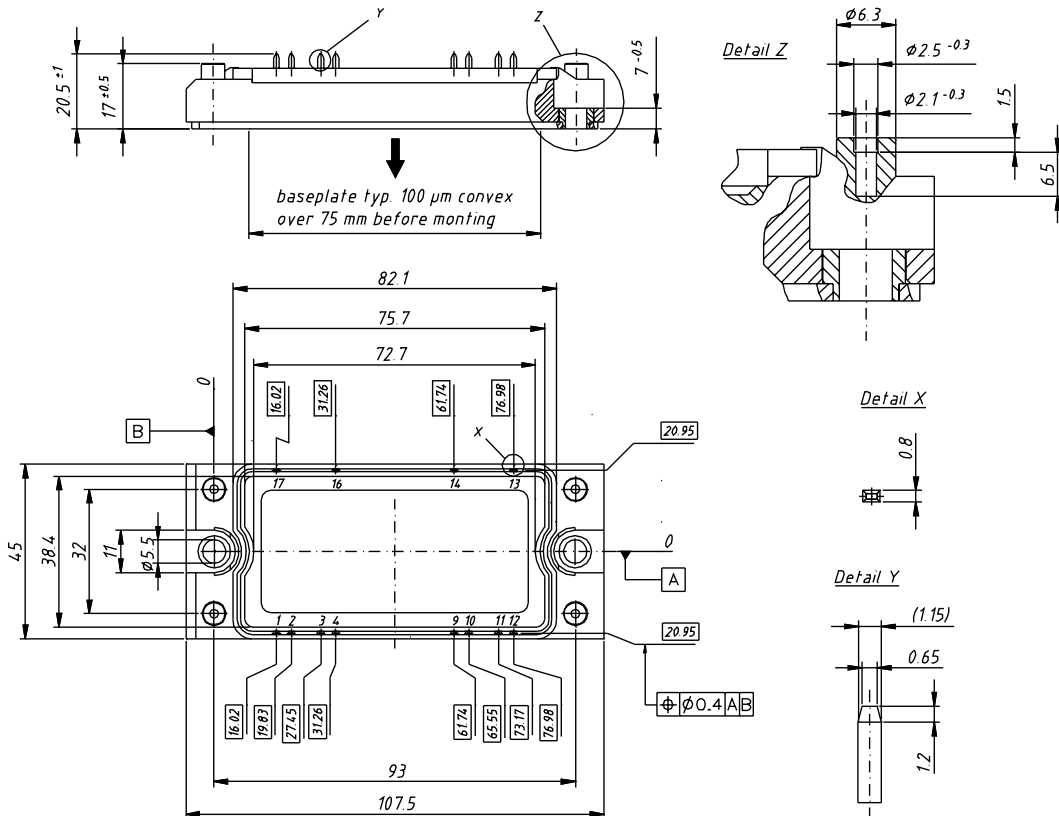
 $T_C = 25^\circ\text{C}$ unless otherwise stated

Circuit Diagram

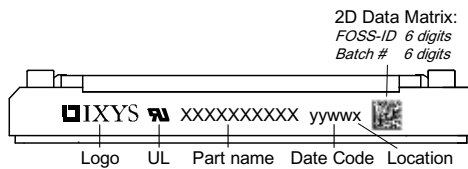


Outline Drawing

Dimensions in mm (1 mm = 0.0394")



Product Marking



Part number

M = Module
I = IGBT
X = XPT
A = standard
61 = Current Rating [A]
H = H~ Bridge
1200 = Reverse Voltage [V]
ED = E2-Pack

| Ordering | Part Name | Marking on Product | Delivering Mode | Base Qty | Ordering Code |
|----------|---------------|--------------------|-----------------|----------|---------------|
| Standard | MIXA61H1200ED | MIXA61H1200ED | Box | 6 | 511060 |

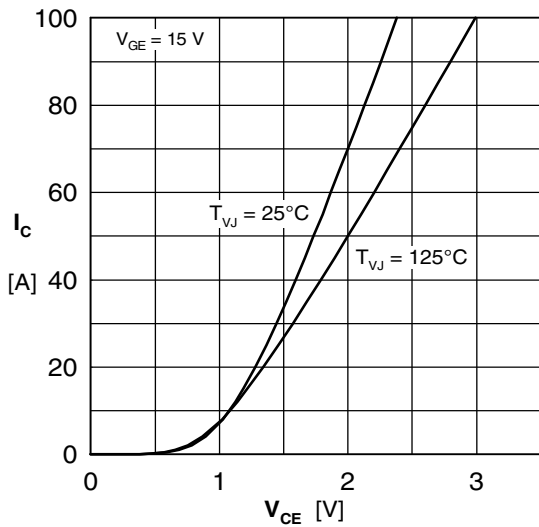
Inverter T1 - T6


Fig. 1 Typ. output characteristics

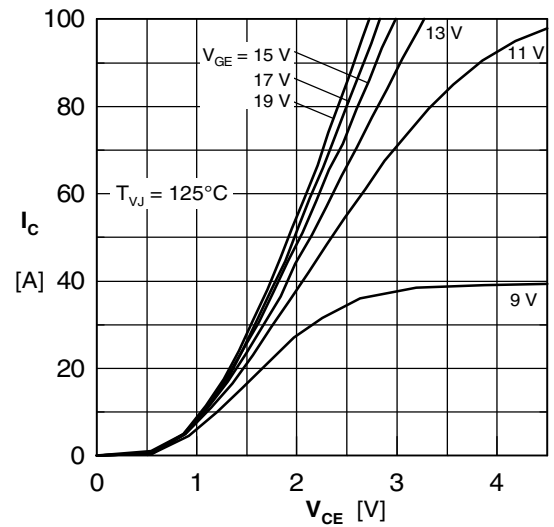


Fig. 2 Typ. output characteristics

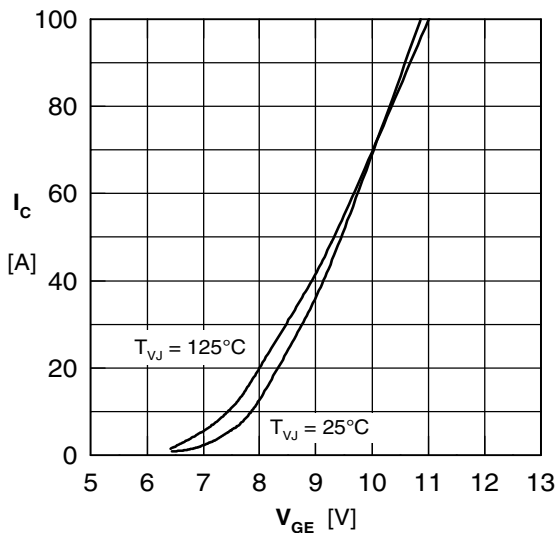


Fig. 3 Typ. transfer characteristics

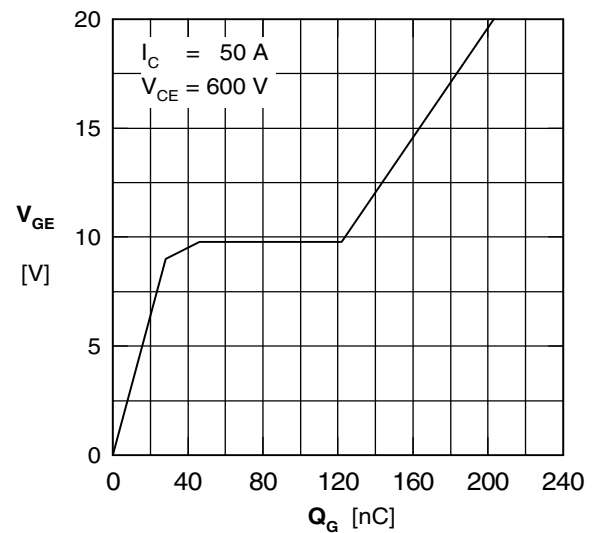


Fig. 4 Typ. turn-on gate charge

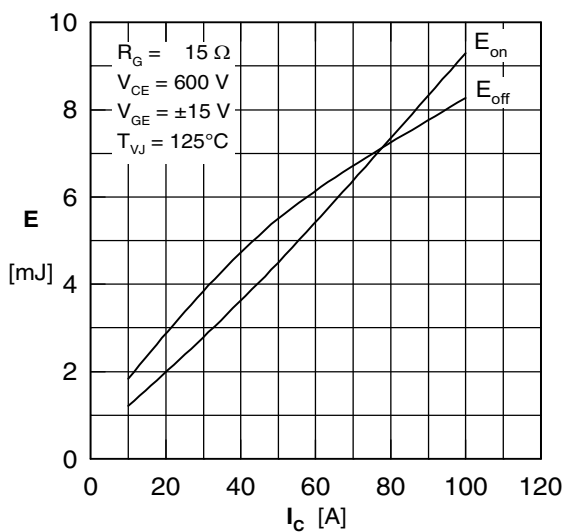


Fig. 5 Typ. switching energy vs. collector current

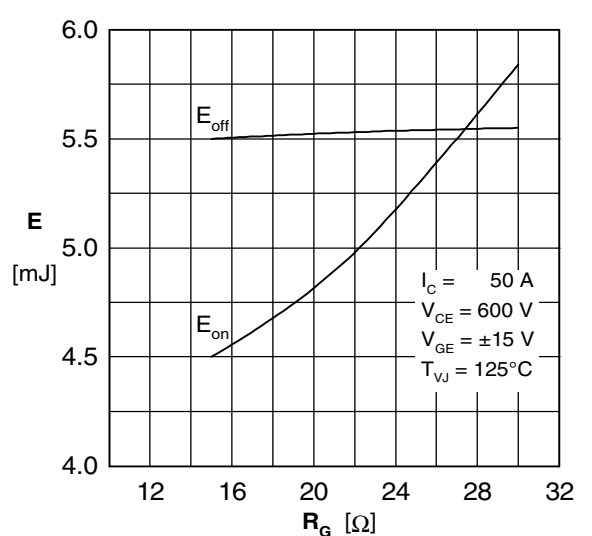


Fig. 6 Typ. switching energy vs. gate resistance

Inverter D1 - D6

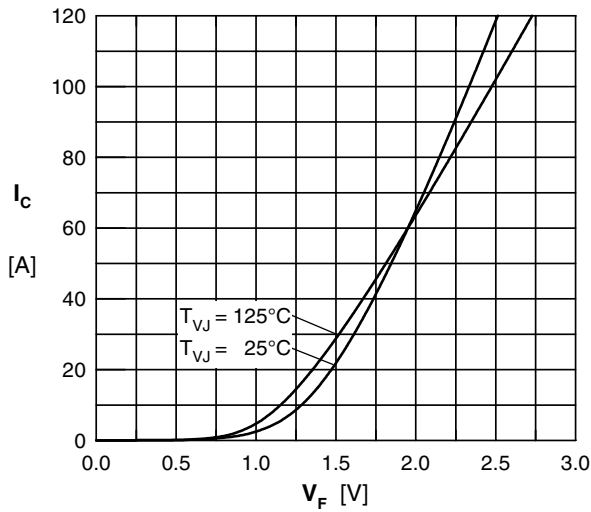


Fig. 7 Typ. Forward current versus V_F

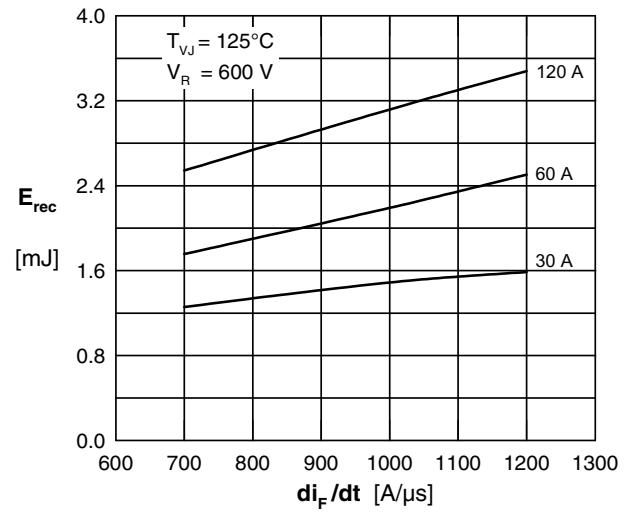


Fig. 8 Typ. recovery energy E_{rec} versus di/dt

| | IGBT | | FRD | |
|---|-------|----------|-------|----------|
| | R_i | τ_i | R_i | τ_i |
| 1 | 0.1 | 0.0025 | 0.137 | 0.0025 |
| 2 | 0.05 | 0.03 | 0.1 | 0.03 |
| 3 | 0.21 | 0.03 | 0.233 | 0.03 |
| 4 | 0.07 | 0.08 | 0.13 | 0.08 |

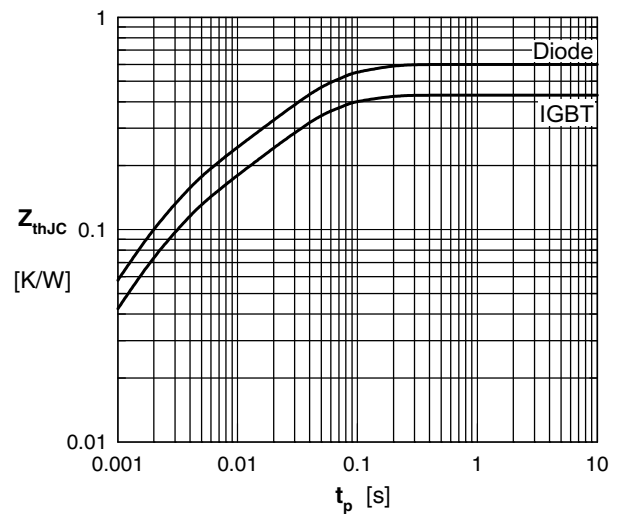


Fig. 9 Typ. transient thermal impedance